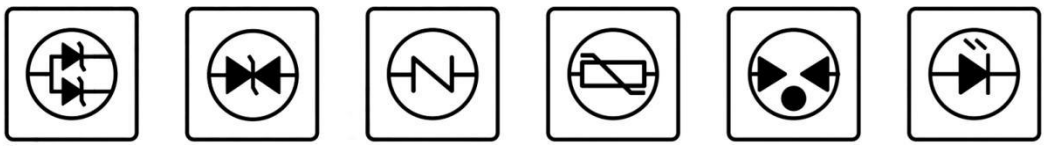
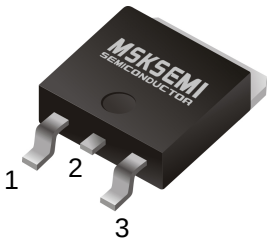
MSKSEMI
SEMICONDUCTOR



Product data sheet

www.msksemi.com



TO-252-2L

1. BASE

2. COLLECTOR

3 .EMITTER

TRANSISTOR (PNP)

FEATURES

Low Speed Switching

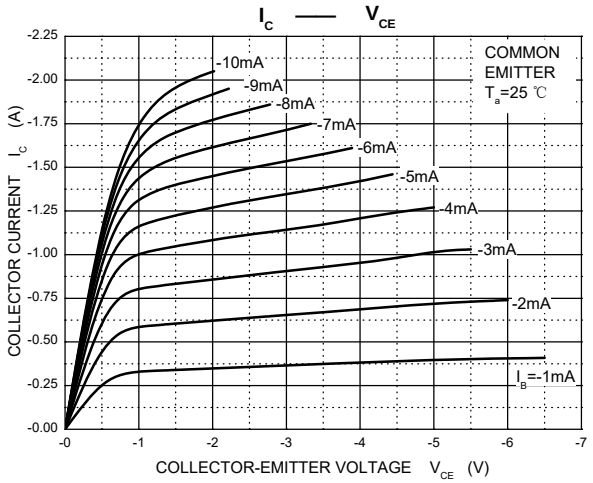
MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

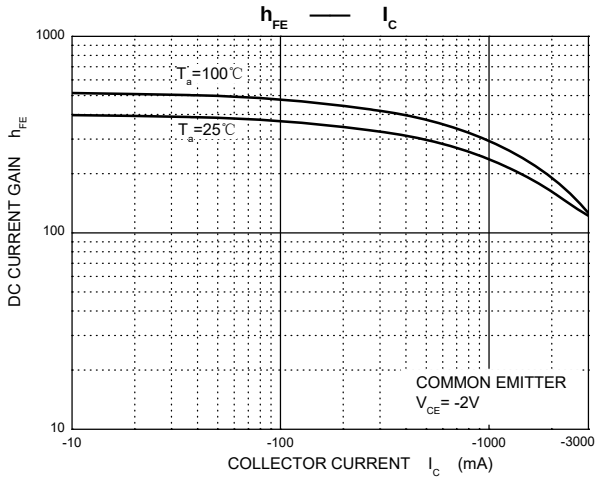
Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current -Continuous	-3	A
P_C	Collector Power Dissipation	1.25	W
$R_{\Theta JA}$	Thermal Resistance, junction to Ambient	100	℃/W
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55-150	℃

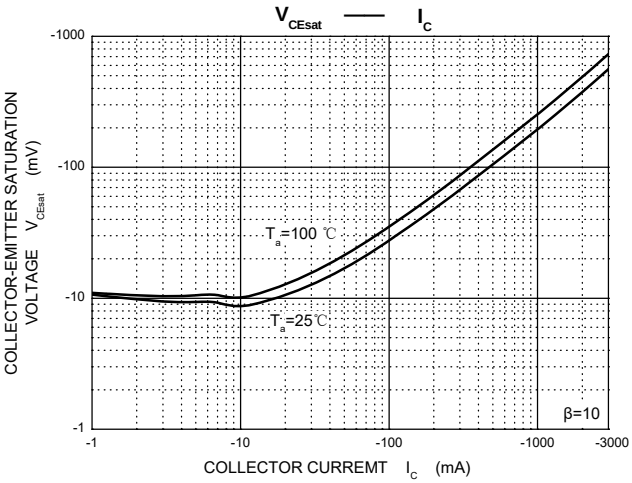
ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

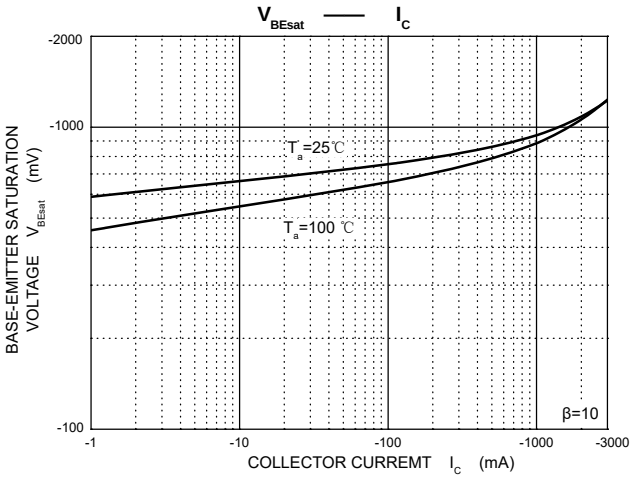
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100μA ,I_E=0	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= -10mA , I_B=0	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= -100μA,I_C=0	-6			V
Collector cut-off current	I_{CBO}	V_{CB}= -40V, I_E=0			-1	μA
Collector cut-off current	I_{CEO}	V_{CE}=-30V, I_B=0			-10	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-6V, I_C=0			-1	μA
DC current gain	h_{FE}	V_{CE}= -2V, I_C= -1A	60		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-2A, I_B= -0.2A			-0.	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-2A, I_B= -0.2A			-1.	V
Transition frequency	f_T	V_{CE}= -5V, I_C=-0.1A f =10MHz	50	8		MHz

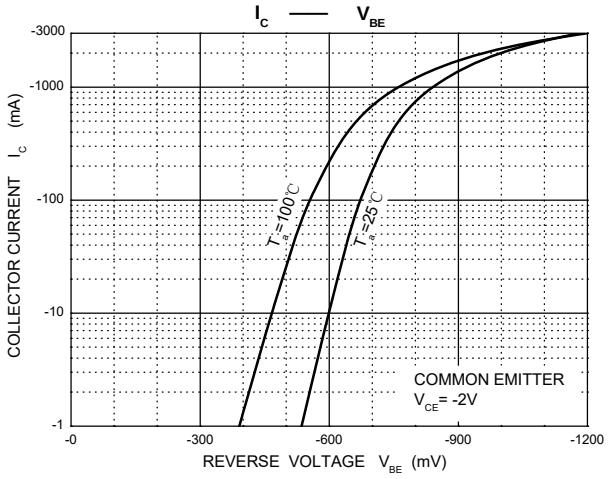
Typical Characteristics

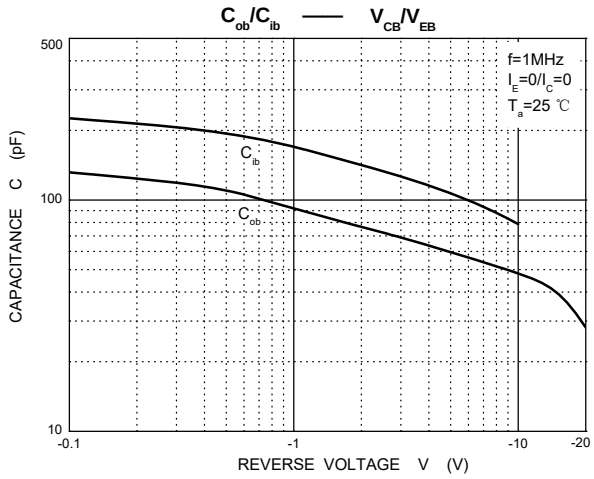


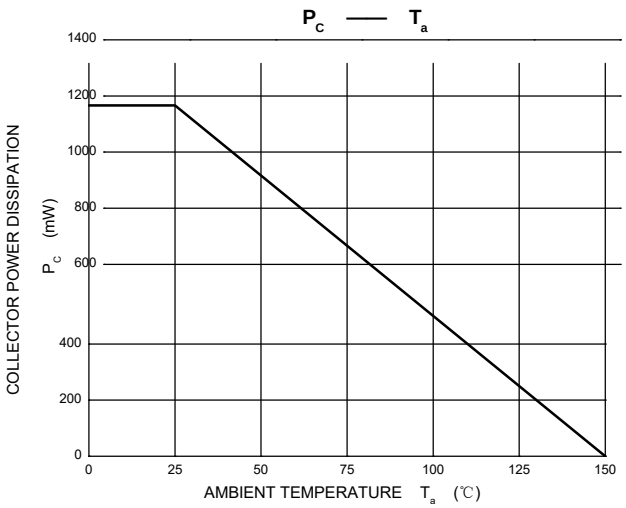




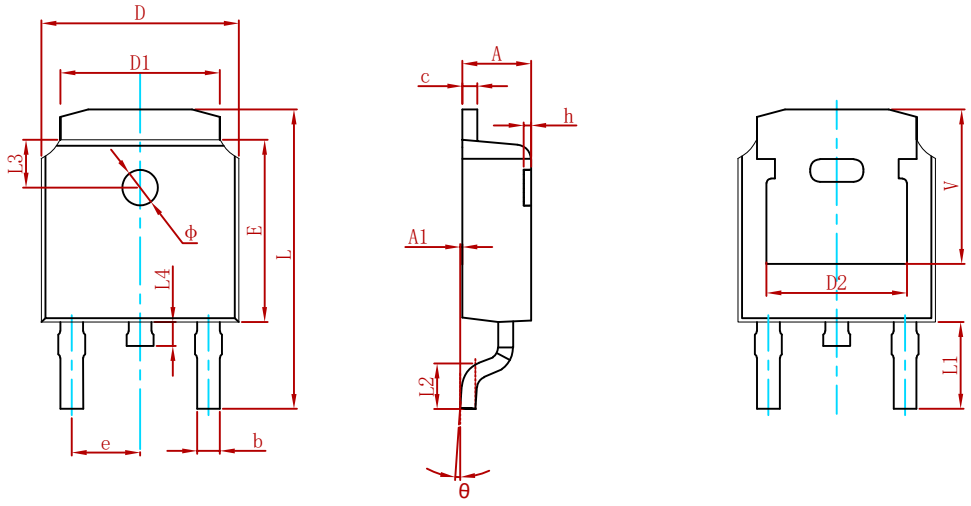






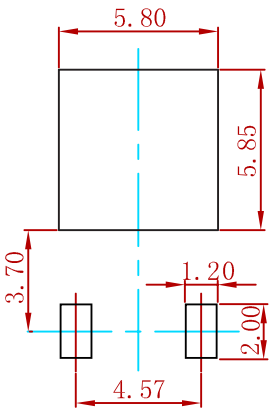


PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	

Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
2SB772	TO-252	2500

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